

SUBSTRATE PROCESSING METHOD, METHOD FOR MANUFACTURING
SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING DEVICE

ABSTRACT

According to the present invention, a film containing a first element and a second element is formed on a substrate by performing: a first step for forming a first layer containing the first element by performing, a first number of times, a cycle that includes (a-1) a step for supplying a first raw-material gas containing the first element to the substrate, and (a-2) a step for supplying a first reaction gas to the substrate; and a second step for forming a second layer containing the first element and the second element by performing, a second number of times, a cycle that includes (b-1) a step for supplying a second raw-material gas containing the first element and a first halogen element to the substrate, (b-2) a step for supplying a third raw-material gas containing a second halogen element and the second element, which is not contained in the first layer, to the substrate after the supply of the second raw-material gas in step (b-1) has been performed for a first period, and (b-3) a step for supplying a second reaction gas to the substrate after the supply of the third raw-material gas in (b-2) has been performed for a second period.

Fig. 4